

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|------|-----------------------------|--|----------------------|----------|
| 1 | BRS | L1 | 219 | rhodes near howard.in. | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 16:45 | |
| 2 | BRS | L2 | 16 | 1 and (well near region) | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 16:46 | |
| 3 | BRS | L3 | 4 | patrick near inna.in. | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 16:46 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|------|---|--|----------------------|----------|
| 4 | BRS | L4 | 0 | mautitzson near richard.in. | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 16:47 | |
| 5 | BRS | L5 | 56 | 438/84.ccls. | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 16:48 | |
| 6 | BRS | L6 | 2976 | (implant\$3) near15 (well near region) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 16:48 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|---|------|-----|------|---|--|----------------------|----------|
| 7 | BRS | L7 | 428 | (implant\$3) near15 (well near region) near25 (transistor) | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 16:49 | |
| 8 | BRS | L8 | 47 | (implant\$3) near15 (well near region) near15 (conductivity) near25 (transistor) | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 17:23 | |
| 9 | BRS | L9 | 156 | (implant\$3) near15 (well) near15 (conductivity) near25 (transistor or gate) near25 (substrate) | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 17:24 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|-------|--|--|----------------------|----------|
| 10 | BRS | L10 | 71 | (implant\$3) near15 (well) near15 (second near conductivity) near25 (transistor or gate) near25 (substrate) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 17:44 | |
| 11 | BRS | L11 | 19124 | (implant\$3) near15 (well) near15 (second near conductivity) near25 (transistor or gate) (first near conductivity) near25 (substrate) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 17:44 | |
| 12 | BRS | L12 | 59 | (implant\$3) near15 (well) near15 (second near conductivity) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 17:57 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|--|--|------------------|----------|
| 13 | BRS | L13 | 804 | (well) near15 (second near conductivity) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate) | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/01 17:57 | |
| 14 | BRS | L14 | 102 | (implant\$3) near15 (well) near15 (first near conductivity) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate) | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/01 19:39 | |
| 15 | BRS | L15 | 7 | (implant\$3) near15 (well) near15 (first near conductivity) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate) near25 (doped) | USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/01 17:58 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|---|--|----------------------|----------|
| 16 | BRS | L16 | 6 | (implant\$3) near15 (well) near15 (dose) near25 (transistor or gate) near15 (first near conductivity) near25 (substrate) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:25 | |
| 17 | BRS | L17 | 60 | (implant\$3) near15 (well) near15 (dose) near25 (transistor or gate) near25 (substrate) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:26 | |
| 18 | BRS | L18 | 24 | (implant\$3) near15 (doped near region) near15 (dose) near25 (transistor or gate) near25 (substrate) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:26 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|--|--|----------------------|----------|
| 19 | BRS | L19 | 2 | (ccd near imager) near15 (electrical near device) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:43 | |
| 20 | BRS | L20 | 3 | (implant\$3 near dose) near15 (doped near region) near15 (below) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:44 | |
| 21 | BRS | L21 | 93 | (implant\$3 near dose) near15 (doped near region) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:46 | |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments |
|----|------|-----|------|--|--|----------------------|----------|
| 22 | BRS | L22 | 78 | (implant\$3 near dose) near15 (doped near region) near15 (dose) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:48 | |
| 23 | BRS | L23 | 6 | (implant\$3 near dose) near15 (doped near region) near15 (p-type) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:49 | |
| 24 | BRS | L24 | 132 | (implant\$3) near15 (doped near region) near15 (p-type) near5 (substrate) | USPAT ; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB | 2004/11/0 1 19:49 | |

| | U | 1 | Document ID | Title | Current OR | Pages |
|---|-------------------------------------|--------------------------|-------------------------|---|------------|-------|
| 1 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20030001175 A1 | Semiconductor device and method for fabricating the same | 257/288 | 47 |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 6627490 B2 | Semiconductor device and method for fabricating the same | 438/200 | 45 |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 6472714 B1 | Semiconductor device in which memory cells and peripheral circuits are provided on the same circuit | 257/371 | 46 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 6429066 B1 | Method for producing a polysilicon circuit element | 438/239 | 40 |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 5981324 A | Methods of forming integrated circuits having memory cell arrays and peripheral circuits therein | 438/210 | 11 |

| | U | 1 | Document ID | Title | Current OR | Pages |
|---|--------------------------|--------------------------|--------------|---|------------|-------|
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 5893740 A | Method of forming a short channel field effect transistor | 438/289 | 7 |